



Features

- High isolation 5000 VRMS
- CTR flexibility available see order information
- DC input with transistor output
- External Creepage ≥ 7.4mm
- Distance Through Isolation ≥ 0.4mm
- Spatial Distance ≥ 7.5mm (S/SL Type)
- Spatial Distance ≥ 8.0mm (M/SLM Type)
- Operating Temperature range 55 °C to 110 °C
- Regulatory Approvals
 - UL UL1577 (E364000)
 - VDE EN60747-5-5(VDE0884-5)
 - CQC GB4943.1, GB8898
 - IEC60065, IEC60950

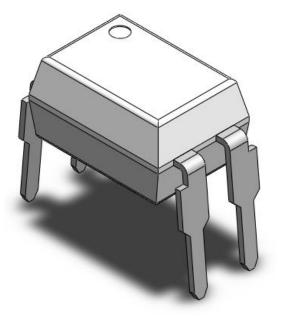
Description

The CT817 series consists of a photo transistor optically coupled to a gallium arsenide Infrared-emitting diode in a 4-lead DIP package different lead forming options.

Applications

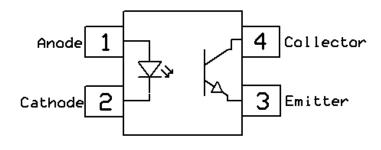
- Switch mode power supplies
- Computer peripheral interface
- Microprocessor system interface

Package Outline



Note: Different lead forming options available. See package dimension.

Schematic





DC Input 4-Pin Phototransistor Optocoupler

Absolute Maximum Rating at 25°C

Symbol	Parameters	Ratings	Units	Notes
Viso	Isolation voltage (AC, 1 minute)	5000	V _{RMS}	
Ртот	Total power dissipation	200	mW	
Topr	Operating temperature	-55 ~ +110	°C	
Тѕтс	Storage temperature	-55 ~ +150	°C	
TsoL	Soldering temperature	260	°C	
Emitter				
I _F	Forward current	60	mA	
I _{F(TRANS)}	Peak transient current (≤1µs P.W,300pps)	1	Α	
V _R	Reverse voltage	6	V	
PD	Emitter power dissipation	100	mW	
Rth _{J-A}	Thermal Resistance Junction-Ambient	350	°C/W	
TJ	Junction temperature	125	°C	
Detector	•	·	·	
PD	Detector power dissipation	150	mW	
Bvceo	Collector-Emitter Breakdown Voltage	35	V	
B _{VECO}	Emitter-Collector Breakdown Voltage	6	V	
lc	Collector Current	50	mA	



DC Input 4-Pin Phototransistor Optocoupler

Electrical Characteristics $T_A = 25$ °C (unless otherwise specified)

Emitter Characteristics

Symbol	Parameters	Test Conditions	Min	Тур	Max	Units	Notes
VF	Forward voltage	I _F =10mA	-	1.24	1.4	V	
I _R Reverse Current		V _R = 6V	-	-	5	μΑ	
Cin	Input Capacitance	f= 1MHz	-	10	30	pF	

Detector Characteristics

Symbol	Parameters	Test Conditions	Min	Тур	Max	Units	Notes
Bvceo	Collector-Emitter Breakdown	Ic= 100μA	35	-	-	V	
B _{VECO}	Emitter-Collector Breakdown	I _E = 100μA	6	-	-	V	
ICEO	Collector-Emitter Dark Current	V _{CE} = 20V, I _F =0mA	-	-	100	nA	

Transfer Characteristics

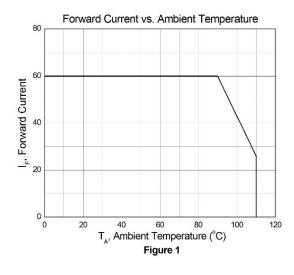
Symbol	Parameters		Test Conditions	Min	Тур	Max	Units	Notes
	CT817 CT817A	CT817		50	-	600		
			80	-	160			
CTR	Current Transfer Ratio	CT817B	I _F = 5mA, V _{CE} = 5V	130	-	260	%	
	Rallo	CT817C		200	-	400		
		CT817D		300	-	600		
V	Collector-Emitter Saturation		I _F = 20mA, I _C = 1mA		0.1	0.2	V	
V _{CE(SAT)}	Voltage		IF- ZUIIA, IC- IIIIA	-	0.1	0.2	V	
Rio	Isolation Resistance		V _{IO} = 500V _{DC}	5x10 ¹⁰	-	-	Ω	
Cıo	Isolation Capacitance		f= 1MHz	-	0.25	1	pF	

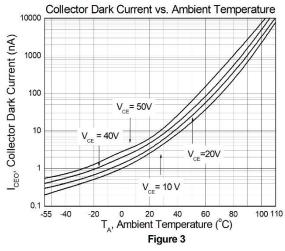
Switching Characteristics

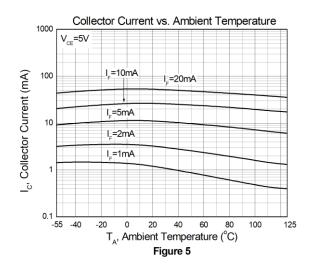
Symbol	Parameters	Test Conditions	Min	Тур	Max	Units	Notes
t _r	Rise Time	I _C = 2mA, V _{CE} = 2V	-	6	18	0	
t _f	Fall Time	R _L = 100Ω	1	8	18	μS	

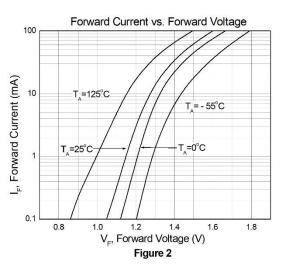


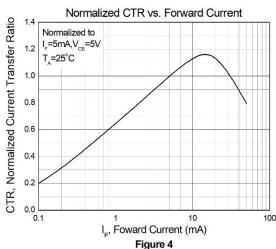
Typical Characteristic Curves

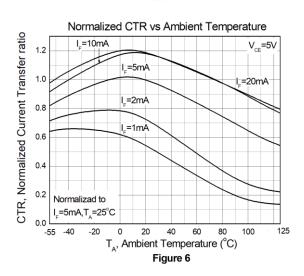






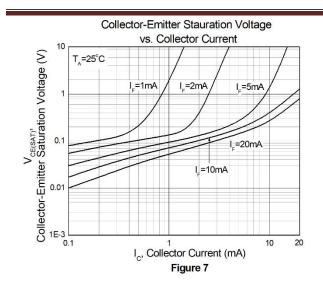


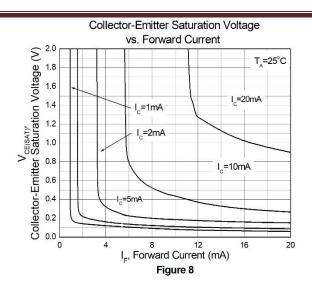


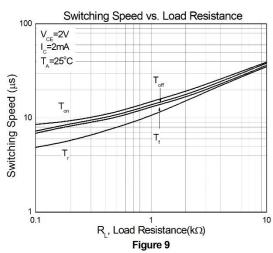


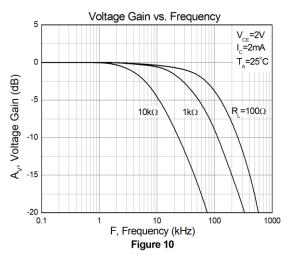


DC Input 4-Pin Phototransistor Optocoupler













Test Circuit

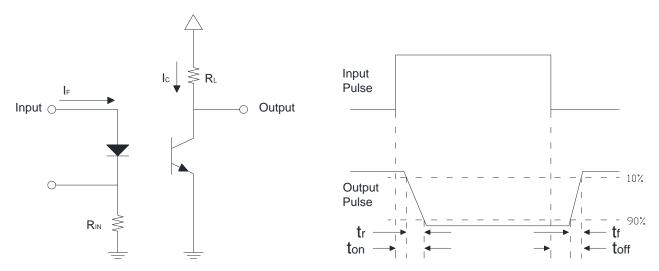
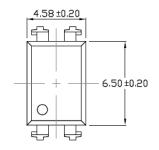


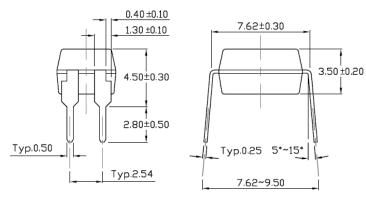
Figure 12: Switching Time Test Circuits



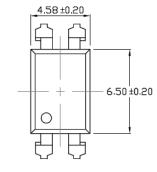
Package Dimension Dimensions in mm unless otherwise stated

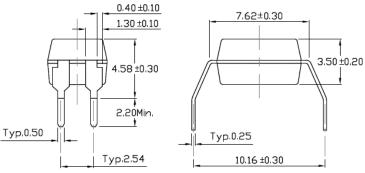
Standard DIP - Through Hole





Gullwing (400mil) Lead Forming – Through Hole (M Type)

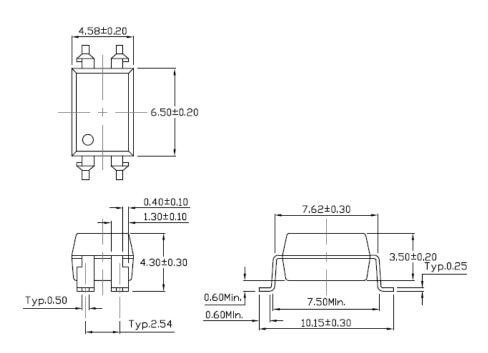




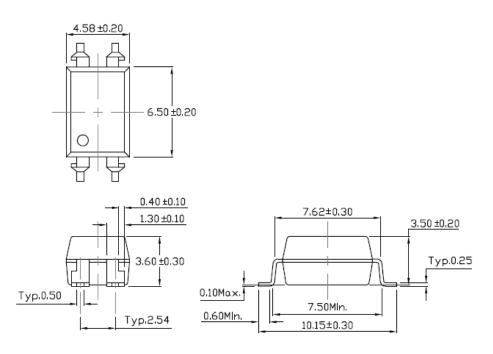




Surface Mount Lead Forming (S Type)



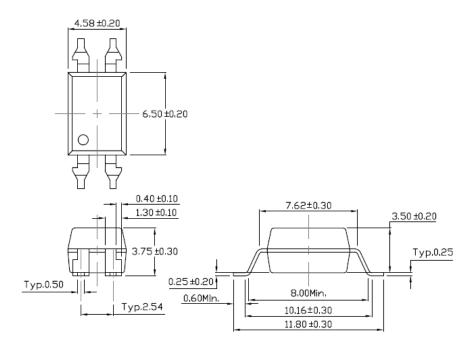
Surface Mount (Low Profile) Lead Forming (SL Type)





DC Input 4-Pin Phototransistor Optocoupler

Surface Mount (Gullwing) Lead Forming (SLM Type)

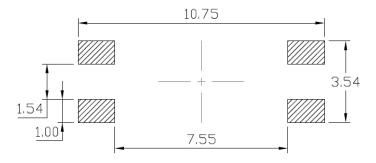




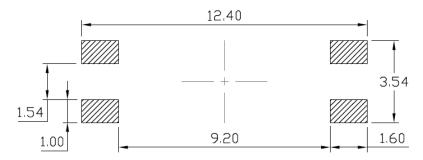


Recommended Solder Mask Dimensions in mm unless otherwise stated

Surface Mount Lead Forming & Surface Mount (Low Profile) Lead Forming



Surface Mount (Gullwing) Lead Forming



Marking Information



Note:

CT : Denotes "CT Micro"

817 : Part NumberR : CTR RankV : VDE OptionY : Fiscal Year

WW : Work Week

K : Manufacturing Code





Ordering Information

CT817X(V)(Y)(Z)-HG

X = Part No. (X=A, B, C, D or None)

V = VDE Option (V or None)

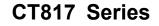
Y = Lead form option (S, SL, M, SLM or none)

Z = Tape and reel option (T1, T2, T3, T4 or none)

H = Lead frame option (H: Iron, None: Copper)

G= Material option (G: Green, None: Non-green)

Option	Description	Quantity
None	Standard 4 Pin Dip	100 Units/Tube
М	Gullwing (400mil) Lead Forming	100 Units/Tube
S(T1)	Surface Mount Lead Forming – With Option 1 Taping	1500 Units/Reel
S(T2)	Surface Mount Lead Forming – With Option 2 Taping	1500 Units/Reel
S(T3)	Surface Mount Lead Forming – With Option 3 Taping	1000 Units/Reel
S(T4)	Surface Mount Lead Forming – With Option 4 Taping	1000 Units/Reel
SL(T1)	Surface Mount (Low Profile) Lead Forming– With Option 1 Taping	1500 Units/Reel
SL(T2)	Surface Mount (Low Profile) Lead Forming – With Option 2 Taping	1500 Units/Reel
SL(T3)	Surface Mount (Low Profile) Lead Forming– With Option 3 Taping	1000 Units/Reel
SL(T4)	Surface Mount (Low Profile) Lead Forming – With Option 4 Taping	1000 Units/Reel
SLM(T1)	Surface Mount (Gullwing) Lead Forming– With Option 1 Taping	1500 Units/Reel
SLM(T2)	Surface Mount (Gullwing) Lead Forming – With Option 2 Taping	1500 Units/Reel

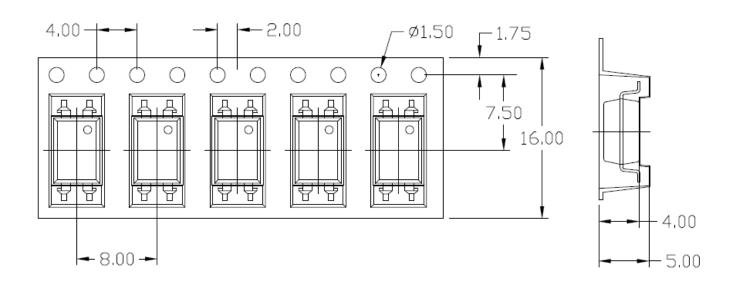




Carrier Tape Specifications Dimensions in mm unless otherwise stated

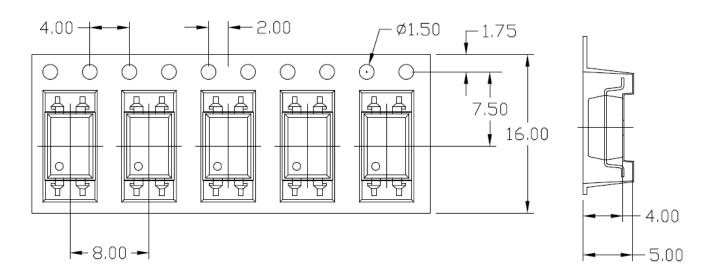
Option S(T1) & SL(T1)

Input Direction



Option S(T2) & SL(T2)

Input Direction

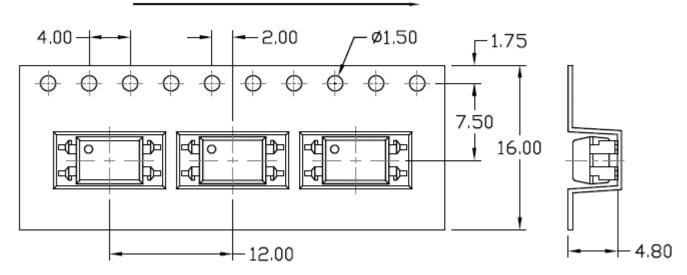






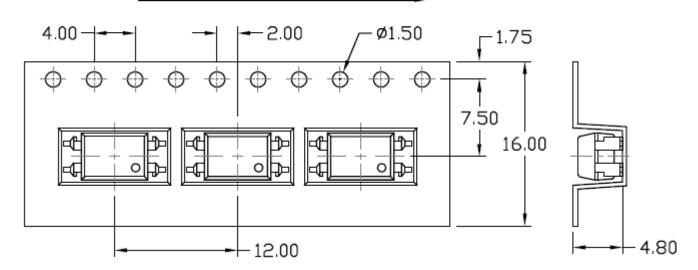
Option S(T3) & SL(T3)

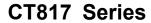
Input Direction



Option S(T4) & SL(T4)

Input Direction

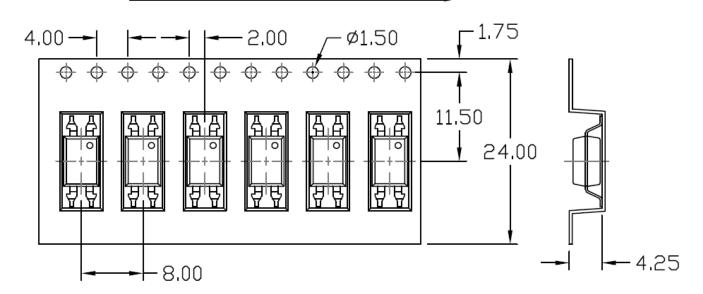






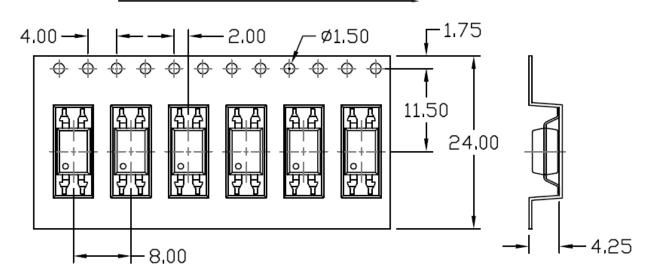
Option SLM(T1)

Input Direction



Option SLM(T2)

Input Direction







Wave soldering (follow the JEDEC standard JESD22-A111)

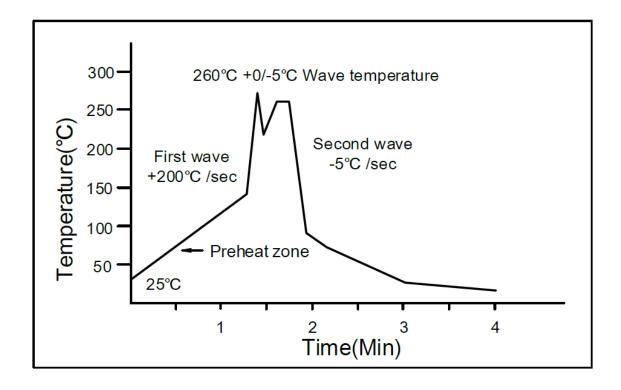
One time soldering is recommended within the condition of temperature.

Temperature: 260+0/-5°C.

Time: 10 sec.

Preheat temperature:25 to 140°C.

Preheat time: 30 to 80 sec.



Iron soldering (follow the standard MIL-STD 202G, Method 210F)

Allow single lead soldering in every single process.

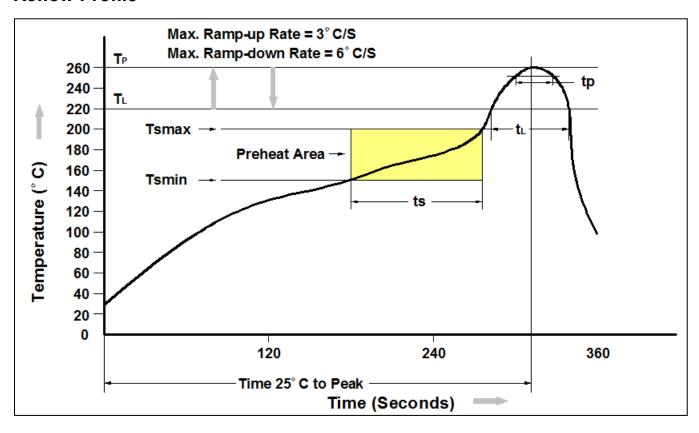
One time soldering is recommended. Temperature: 350+±10°C

Time: 5 sec max.





Reflow Profile



Profile Feature	Pb-Free Assembly Profile
Temperature Min. (Tsmin)	150°C
Temperature Max. (Tsmax)	200°C
Time (ts) from (Tsmin to Tsmax)	60-120 seconds
Ramp-up Rate (t∟ to t _P)	3°C/second max.
Liquidous Temperature (T _L)	217°C
Time (t _L) Maintained Above (T _L)	60 – 150 seconds
Peak Body Package Temperature	260°C +0°C / -5°C
Time (t _P) within 5°C of 260°C	30 seconds
Ramp-down Rate (T _P to T _L)	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.



DC Input 4-Pin Phototransistor Optocoupler

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